Anna Chernikova

List of Publications by Year
in descending order

36 papers	1,388 citations	489802 18 h-index	371746 37 g-index
39 all docs	39 docs citations	39 times ranked	1357 citing authors

#	Article	IF	Citations
1	Origin of the retention loss in ferroelectric Hf0.5Zr0.5O2-based memory devices. Acta Materialia, 2021, 204, 116515.	3.8	36
2	Charge Transport Mechanism in Atomic Layer Deposited Oxygenâ€Ðeficient TaO x Films. Physica Status Solidi (B): Basic Research, 2021, 258, 2000432.	0.7	4
3	Dynamic imprint recovery as an origin of the pulse width dependence of retention in Hf0.5Zr0.5O2-based capacitors. Applied Physics Letters, 2021, 119, .	1.5	12
4	Atomic Layer Deposition of Ultrathin Tungsten Oxide Films from WH₂(Cp)₂ and Ozone. Journal of Physical Chemistry C, 2021, 125, 21663-21669.	1.5	4
5	Influence of the Annealing Temperature and Applied Electric Field on the Reliability of TiN/Hf_{0.5}Zr_{0.5}O₂/TiN Capacitors. ACS Applied Electronic Materials, 2021, 3, 4317-4327.	2.0	12
6	Thickness-Dependent Structural and Electrical Properties of WS₂ Nanosheets Obtained via the ALD-Grown WO₃ Sulfurization Technique as a Channel Material for Field-Effect Transistors. ACS Omega, 2021, 6, 34429-34437.	1.6	16
7	Impact of the Atomic Layer-Deposited Ru Electrode Surface Morphology on Resistive Switching Properties of TaO_x-Based Memory Structures. ACS Applied Materials & Interfaces, 2020, 12, 55331-55341.	4.0	14
8	Influence of ALD Ru bottom electrode on ferroelectric properties of Hf0.5Zr0.5O2-based capacitors. Applied Physics Letters, 2020, 117, .	1.5	15
9	Resistance Switching Peculiarities in Nonfilamentary Selfâ€Rectified TiN/Ta₂O₅/Ta and TiN/HfO₂/Ta₂O₅/Ta Stacks. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900952.	0.8	18
10	The Effect of Five-Day Dry Immersion on the Nervous and Metabolic Mechanisms of the Circulatory System. Frontiers in Physiology, 2020, 11, 692.	1.3	6
11	Two-Dimensional and Screw Growth of MoS2 Films in the Process of Chemical Deposition from the Gas Phase. Russian Journal of Applied Chemistry, 2019, 92, 596-601.	0.1	2
12	Synthesis of Large Area Two-Dimensional MoS₂ Films by Sulfurization of Atomic Layer Deposited MoO₃ Thin Film for Nanoelectronic Applications. ACS Applied Nano Materials, 2019, 2, 7521-7531.	2.4	34
13	Temperature controlled Ru and RuO2 growth via O* radical-enhanced atomic layer deposition with Ru(EtCp)2. Journal of Chemical Physics, 2019, 151, 204701.	1.2	18
14	Identification of the nature of traps involved in the field cycling of Hf0.5Zr0.5O2-based ferroelectric thin films. Acta Materialia, 2019, 166, 47-55.	3.8	76
15	Mitigating wakeup effect and improving endurance of ferroelectric HfO2-ZrO2 thin films by careful La-doping. Journal of Applied Physics, 2019, 125, .	1.1	110
16	Ferroelectricity in Hf_{0.5}Zr_{0.5}O₂ Thin Films: A Microscopic Study of the Polarization Switching Phenomenon and Field-Induced Phase Transformations. ACS Applied Materials & Interfaces, 2018, 10, 8818-8826.	4.0	55
17	Improved Ferroelectric Switching Endurance of La-Doped Hf_{0.5}Zr_{0.5}O₂ Thin Films. ACS Applied Materials & Interfaces, 2018, 10, 2701-2708.	4.0	207
18	La-doped Hf0.5Zr0.5O2 thin films for high-efficiency electrostatic supercapacitors. Applied Physics Letters, 2018, 113, .	1.5	43

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19	Short-Range Order in Amorphous and Crystalline Ferroelectric Hf0.5Zr0.5O2. Journal of Experimental and Theoretical Physics, 2018, 126, 816-824.	0.2	6
20	Electron transport across ultrathin ferroelectric Hf0.5Zr0.5O2 films on Si. Microelectronic Engineering, 2017, 178, 250-253.	1.1	61
21	Leakage Currents Mechanism in Thin Films of Ferroelectric Hf_{0.5}Zr_{0.5}O₂. ECS Transactions, 2017, 75, 123-129.	0.3	13
22	Low temperature plasmaâ€enhanced ALD TiN ultrathin films for Hf_{0.5}Zr_{0.5}O₂â€based ferroelectric MIM structures. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700056.	0.8	20
23	Ferroelectric properties of lightly doped La:HfO2 thin films grown by plasma-assisted atomic layer deposition. Applied Physics Letters, 2017, 111, .	1.5	69
24	Effect of Polarization Reversal in Ferroelectric TiN/Hf_{0.5}Zr_{0.5}O₂/TiN Devices on Electronic Conditions at Interfaces Studied in Operando by Hard X-ray Photoemission Spectroscopy. ACS Applied Materials & Interfaces, 2017, 9, 43370-43376.	4.0	46
25	Leakage currents mechanism in thin films of ferroelectric Hf_{0.5}Zr_{0.5}O₂. Journal of Physics: Conference Series, 2017, 864, 012002.	0.3	4
26	Fully ALD-grown TiN/Hf0.5Zr0.5O2/TiN stacks: Ferroelectric and structural properties. Applied Physics Letters, 2016, 109, .	1.5	64
27	Ferroelectric properties of full plasma-enhanced ALD TiN/La:HfO2/TiN stacks. Applied Physics Letters, 2016, 108, .	1.5	79
28	Charge transport in thin layers of ferroelectric Hf0.5Zr0.5O2. Russian Microelectronics, 2016, 45, 350-356.	0.1	1
29	Investigation of the properties and manufacturing features of nonvolatile FRAM memory based on atomic layer deposition. Russian Microelectronics, 2016, 45, 262-269.	0.1	8
30	Ultrathin Hf_{0.5}Zr_{0.5}O₂ Ferroelectric Films on Si. ACS Applied Materials & Interfaces, 2016, 8, 7232-7237.	4.0	186
31	Charge transport mechanism in thin films of amorphous and ferroelectric Hf0.5Zr0.5O2. JETP Letters, 2015, 102, 544-547.	0.4	25
32	Effect of dielectric stoichiometry and interface chemical state on band alignment between tantalum oxide and platinum. Applied Physics Letters, 2015, 107, .	1.5	14
33	Structural, chemical and electrical properties of ALDâ€grown Hf_xAl_{1â€“x}O_y thin films for MIM capacitors. Physica Status Solidi (B): Basic Research, 2015, 252, 701-708.	0.7	4
34	Confinement-free annealing induced ferroelectricity in Hf0.5Zr0.5O2 thin films. Microelectronic Engineering, 2015, 147, 15-18.	1.1	64
35	Atomic layer deposition of Al2O3 and AlxTi1â^'xOy thin films on N2O plasma pretreated carbon materials. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, 01A135.	0.9	4
36	Correlation between bioactivity and structural properties of titanium dioxide coatings grown by atomic layer deposition. Applied Surface Science, 2012, 258, 3415-3419.	3.1	35